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# The effect of hadron irradiation on the electrical properties of particle detectors made from various silicon materials

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## Contents

| List of figures   |
|---|
| List of tables  |
| Introduction  |
| Chapter 1 – Motivation and framework                            |
| 1.1 The Large Hadron Collider (LHC)                             |
| 1.2 Physics at LHC  |
| 1.2.1 The ATLAS and CMS experiments                             |
| 1.2.2 The radiation environment                                 |
| 1.3 The ROSE (CERN-R&D 48) collaboration27                      |
| <b>Chapter 2 – Basic Features of Silicon Detectors</b>          |
| 2.1 General principles of semiconductor physics                 |
| 2.2 The p-n junction  |
| 2.3 Silicon mono-crystal fabrication and detector manufacturing |
| 2.3.1 Crystal growth methods 41                                 |
| 2.3.2 Detector manufacturing                                    |
| 2.4 Operation of silicon detectors                              |
| 2.4.1 Biasing features  |
| 2.4.2 Particle detection  |
| Chapter 3 – Radiation damage effects                            |
| 3.1 The radiation damage mechanism54                            |
| 3.2 Changes in detectors properties                             |
| 3.2.1 Reverse Current   |
| 3.2.2 Effective doping concentration $(N_{eff})$                |
| 3.2.3 Charge Collection Efficiency69                            |
| Chapter 4 – Experimental methods                                |
| 4.1 C-V measurements  |
| 4.2 I-V measurements  |
| 4.3 Charge Collection Measurements                              |

| 4.3.1 β particles  |    |
|--|----|
| 4.3.2 Low range particles: $\alpha$ particles and low energy protons |    |
| 4.3.3 Red light  |    |
| 4.4 Carrier lifetime measurement                                     | 93 |
| 4.5 Irradiation facilities   | 95 |
| 4.4.1 Proton Irradiation Facility                                    | 95 |
| 4.4.2 Neutron Irradiation Facility                                   |    |

## Chapter 5 – Materials

| 5.1 Impurities  |     |
|---|-----|
| 5.1.1 Measurement techniques of the impurity concentration    | 100 |
| 5.1.2 Introduction of impurities in the silicon ingot         | 101 |
| 5.1.3 The impurity diffusion experiment                       | 102 |
| 5.1.4 Neutron transmutation doping of silicon                 |     |
| 5.2 Overview of the materials                                 | 109 |
| 5.3 Devices   |     |
| Chapter 6 – Experimental results                              |     |
| 6.1 Diodes before irradiation                                 | 114 |
| 6.2 Proton irradiations                                       | 116 |
| 6.2.1 $N_{eff}$ as a function of the fluence                  | 116 |
| 6.2.2 $N_{eff}$ as a function of the time after irradiation   |     |
| 6.2.3 Reverse current as a function of the fluence            | 122 |
| 6.3 Neutron irradiations                                      | 124 |
| 6.3.1 $N_{eff}$ as a function of the fluence                  | 127 |
| 6.3.2 $N_{eff}$ as a function of the time after irradiation   | 131 |
| 6.3.3 Reverse current as a function of the fluence            | 132 |
| 6.4 Charge collection efficiency as a function of the fluence | 134 |
| 6.5 Discussion  |     |

| Chapter 7 – Evolution of the active volume in irradiated   | l detectors |
|--|-------------|
| 7.1 Charge collection from low range particle illumination | 142         |
| 7.2 Charge collection from red LED light illumination      | 147         |
| 7.3 Discussion   |             |
| Conclusion   | 165         |
| APPENDIX A - Experimental set-ups                          | 167         |
| APPENDIX B - The diffusion theory in silicon               | 171         |
| References   | 174         |

# List of figures

## Chapter 1

| Fig. 1     | The LEP/LHC tunnel map and (b) the CERN accelerator system                 | 20 |
|------------|--|----|
| Fig. 1.1   | Cross section of the LHC/LEP tunnel. LEP magnet is hosted above the        |    |
|            | double-coil LHC magnet   | 21 |
| Fig. 1.2   | Cross section for various processes expected in proton-proton interactions |    |
|            | as a function of the centre-of-mass energy $\sqrt{s}$                      | 23 |
| Fig. 1.3   | (a) The CMS detector (b) The ATLAS detector.                               | 25 |
| Fig. 1.4   | (a) The CMS and (b) ATLAS inner trackers with Si pixels, SemiConductor     |    |
|            | (Si) Tracker, and TRT (Transition Radiation Tracker)                       | 26 |
| Fig. 1.5 - | Neutron and charged fluxes per year at different radii in the CMS tracking |    |
|            | cavity   | 27 |

| Fig. 2.1 | Schematic band diagram for (a) n-type and (b) p-type semiconductor. $E_D = energy$    |     |
|----------|---|-----|
|          | level of the donor impurity; $E_A = energy$ level of the acceptor impurity            | 2   |
| Fig. 2.2 | Band diagram of (a) uniformly doped p-type and n-type silicon (b) after               |     |
|          | the junction formation  | 3   |
| Fig. 2.3 | Schematic energy band diagram of a p-n junction under external bias (a)               |     |
|          | forward bias (b) reverse bias   | 5   |
| Fig. 2.4 | Ideal I-V characteristic of a silicon diode   | 7   |
| Fig. 2.5 | Processes at an intermediate defect level: (a) generation (b) recombination (         | (c) |
|          | trapping (d) compensation   |     |
| Fig. 2.6 | The capacitance-voltage characteristic of a $p^+$ -n junction                         | )   |
| Fig. 2.7 | Depletion region of a $p^+$ -n junction: (a) $V_1 < V_{FD}$ , (b) $V_2 \ge V_{FD}$ 40 | )   |
| Fig. 2.8 | CERN2 mask for planar device production. This mask is adapted to process              |     |
|          | <i>3" or 4" wafers (internal and external circles respectively).</i>                  | 5   |

| Fig. 2.9  | Basic steps for the planar fabrication of a $p^+$ -n- $n^+$ detector              | 6  |
|-----------|---|----|
| Fig. 2.10 | Basic steps for the mesa fabrication of diodes                                    | 7  |
| Fig. 2.11 | Effect of the guard ring $(G-R)$ contacting on the delimitation on the electric   |    |
|           | field region (a) G-R floating (b) G-R biased                                      | 49 |
| Fig. 2.12 | C-V characteristic of an irradiated planar diode. The decrease of the capacitance |    |

above full depletion is due to the lateral extension of the depleted volume...... 50

## Chapter 3

| Fig. 3.1  | Diagram of some defects in the silicon crystal lattice due to point defect                |
|-----------|---|
|           | complexes   |
| Fig. 3.2  | Picture of a typical recoil-atom track with formation of final highly damaged             |
|           | regions (clusters) as a consequence of heavy-particle irradiation [3.2]                   |
| Fig. 3.3  | Displacement damage cross section as a function of energy for various particle            |
|           | <i>in silicon</i> [3.15]  |
| Fig. 3.4  | The current characteristic as function of the square root of the reverse bias. The        |
|           | reverse current is proportional to the depleted volume until full depletion               |
| Fig. 3.5  | Radiation damage constant, $\alpha$ , as a function of time after irradiation for silicon |
|           | detectors irradiated and stored at various temperatures [3.20]63                          |
| Fig. 3.6  | $N_{eff}(V_{FD})$ as a function of pion fluence [3.28]                                    |
| Fig. 3.7  | Resistivity as a function of fluence (1 MeV neutrons) [3.32] 67                           |
| Fig. 3.8  | Depletion voltage (normalised to 300 $\mu$ m thickness) versus time after irradiation     |
|           | at room temperature for various high resistivity silicon detectors [2.6]                  |
| Fig. 3.9  | Charge collection efficiency as a function of 24 GeV/c proton fluence [3.20] 70           |
| Fig. 3.10 | $V_{FD}$ changes as a function of 24 GeV/c proton fluence for detector irradiated at      |
|           | various temperatures [3.20]   |

## Chapter 4

Fig. 4.1 (a)  $1/C^2$  vs bias for a 200  $\mu$ m thick non-irradiated diode.  $N_{eff}$ , calculated from

|           | $V_{FD}$ , is 7.5 · 10 <sup>12</sup> cm <sup>-3</sup> (b) $N_{eff}$ profile vs depth.              | 73 |
|-----------|--|----|
| Fig. 4.2  | (a) $1/C^2$ vs bias for a 300 $\mu$ m thick non-irradiated low resistivity (180 $\Omega$ cm) diode | 2. |
|           | The detector breakes down before full depletion. (b) $N_{eff}$ profile vs depth. The               |    |
|           | average value of $N_{eff}$ corresponds to the nominal resistivity. The calculated $V_{FD}$         |    |
|           | <i>is</i> ≈ 1900 V   | 75 |
| Fig. 4.3  | Typical C-V characteristics with the frequency as a parameter for (a) non-irradiat                 | ed |
|           | and (b) irradiated diodes [4.5].   | 76 |
| Fig. 4.4  | (a) C-V characteristic of an irradiated type-inverted diode. (b) $N_{eff}$ profile                 |    |
|           | versus depth   | 77 |
| Fig. 4.5  | Leakage current as a function of the reverse bias for variously irradiated silicon                 |    |
|           | diodes with floating and biased guard ring. The reverse current for the non                        |    |
|           | irradiated diode is the same with and without G-R  | 81 |
| Fig. 4.6  | The volume reverse current as a function of fluence measured with and without                      |    |
|           | bias on the G-R  | 82 |
| Fig. 4.7  | Generation of carriers along the path of particle tracks and electric field                        |    |
|           | distribution in the silicon diode  | 83 |
| Fig. 4.8  | Ideal pulse shape for (a) electron injection (junction side) and (b) hole injection                |    |
|           | (ohmic side) of an n-type silicon detector. $V_{FD} \ge V_1 \ge V_2$                               | 86 |
| Fig. 4.9  | CC curve as a function of the square root of bias in the case of $eta$ particle                    |    |
|           | Illumination   | 87 |
| Fig. 4.10 | ) Landau distribution of the energy loss of a MIP in a 300 $\mu m$ thick silicon                   |    |
|           | detector. The most probable value is $\approx 80$ keV  | 88 |
| Fig. 4.11 | Averaged signal pulse shape and integral of the signal induced by $eta$ particles in               |    |
|           | a 307 µm thick silicon detector  | 88 |
| Fig. 4.12 | 2. Energy loss of 1.7 MeV protons in silicon as a function of the path (Bragg's                    |    |
|           | curve) and integrated energy loss as a function of the depletion depth in case of                  |    |
|           | (a) front injection and (b) rear injection   | 89 |
| Fig. 4.13 | Simulated charge collection for front (a) and rear (b) illumination with 1.7 MeV                   |    |
|           | protons in a silicon detector with $V_{FD} = 120$ volts  | 90 |
| Fig. 4.14 | Example of (a) energy loss spectrum and (b) signal pulse shape and integral of the                 | ıe |

|           | signal of an $\alpha$ particle in a fully depleted silicon diode                              | 91   |
|-----------|---|------|
| Fig. 4.15 | Ionisation as a function of depth for red (670 nm) light in silicon                           | 92   |
| Fig. 4.16 | Comparison between the V <sub>FD</sub> measurements obtained with the C-V and the $\beta$ cha | arge |
| colle     | ection (C.C.) methods on the same diode irradiated with 24 GeV/c protons                      | 93   |
| Fig 4.17  | (a) Reverse recovery circuit schematic (b) current and (c) voltage waveforms. At              |      |
|           | $t = 0, \Delta V_d$ is due to the drop on the resistance $R: \Delta V_d = RI_r$ .             | 94   |
| Fig. 4.18 | Reverse recovery signal for a non-irradiated planar diode. The minority carrier               |      |
|           | lifetime is 70 µs   | 95   |
| Fig. 4.19 | Beam relative intensity profile (a) front view (b) 3-d view. X is the horizontal              |      |
|           | co-ordinate and Y is the vertical co-ordinate.  | 96   |
| Fig. 4.20 | Sketch of the detector alignment in the proton beam   | 97   |
| Fig. 4.21 | Fluence (24GeV/c protons) versus Secondary Emission Chamber (SEC) counts                      | 97   |

| Fig. 5.1 | Calculated diffusion profile of P and B for diffusion during 3h at $1200^{\circ}C$ 10        | 12 |
|----------|--|----|
| Fig. 5.2 | Boron and phosphorus concentrations versus depth in a mesa diode, measured by                |    |
|          | the spreading resistance method 10   | 4  |
| Fig. 5.3 | Phosphorus and boron profiles obtained by SIMS from a mesa sample: (a) junction              |    |
|          | $(p^+)$ side (b) ohmic $(n^+)$ side  | 4  |
| Fig. 5.4 | Resistivity profile of a mesa diode before and after two successive annealing steps          |    |
|          | of 1 h at 800 °C in $H_2$ and normal atmosphere. Measurements performed by                   |    |
|          | <i>ITME</i> 10   | 5  |
| Fig. 5.5 | Oxygen and carbon SIMS profiles in a mesa diode10  | 5  |
| Fig. 5.6 | Calculated concentration profiles for (a) C and (b) Sn in silicon for different              |    |
|          | temperatures and times   | 6  |
| Fig. 5.7 | Oxygen profile in (a) a mesa detector (3h at 1200 $^{\circ}$ C) and (b) a sample diffused at |    |
|          | <i>Technion (20h at 1150 °C)</i> 10  | 7  |
| Fig. 5.8 | Calculated oxygen profile for different diffusion time at 1150 $^{\circ}C$                   | 7  |
| Fig. 5.9 | SIMS profile of (a) O and (b) C concentration in O-diffused wafers #8 and #10 10             | 9  |
|          |  |    |

| Fig. 5.10 Oxygen and carbon concentration profiles measured by SIMS for material #14 | . 110 |
|--|-------|
|--|-------|

| Fig. 5.12 | Simulated distribution of the implanted (a) P and (b) B ions for the ohmic and |       |
|-----------|--|-------|
|           | junction side formation in the planar process                                  | . 112 |

| Fig. 6.1  | Energy spectra, recorded by an ADC, of $\beta^{-}$ particles from <sup>106</sup> Ru in overdepleted (a)                      |
|-----------|--|
|           | mesa and (b) planar diodes114  |
| Fig. 6.2  | Energy of impinging protons versus ADC channel for mesa and planar non   |
|           | irradiated diodes 115  |
| Fig. 6.3  | $N_{eff}$ versus fluence for standard (#5) and weakly oxygenated (#6) diodes processed                                       |
|           | <i>by SINTEF</i>   |
| Fig. 6.4  | $N_{e\!f\!f}$ versus fluence for standard (#4, #5) and weakly oxygenated (#6) diodes. #4                                     |
|           | is processed by ITE, #5 and #6 by SINTEF 117   |
| Fig. 6.5  | $N_{eff}$ versus fluence for standard diodes with a different starting resistivity 118                                       |
| Fig. 6.6  | N <sub>eff</sub> versus fluence for epitaxial planar n-type diodes (#17, #18, #19) 118                                       |
| Fig. 6.7  | $N_{eff}$ versus fluence for mesa standard (#5) and weakly oxygenated diodes (#6) 119  |
| Fig. 6.8  | $N_{eff}$ versus fluence for mesa epitaxial (a) n-type and (b) p-type diodes   |
| Fig. 6.9  | Comparison of $N_{eff}$ versus fluence between planar and mesa diodes: (a) standard  |
|           | FZ and (b) epitaxial diodes 120  |
| Fig. 6.10 | $N_{\rm eff}$ versus annealing time (room temperature equivalent) for planar and mesa  |
|           | diodes made from materials #5 and #6 and for two different final fluences: (a)   |
|           | $1.1 \cdot 10^{14} \text{ cm}^{-2}$ , (b) $1.9 \cdot 10^{14} \text{ cm}^{-2}$ . Picture (c) is the same as (b)but plotted in |
|           | logarithmic scale to evidence the beneficial annealing (irradiation April '97)121  |
| Fig. 6.11 | $N_{\mathrm{eff}}$ versus annealing time (room temperature equivalent) for planar and  |
|           | mesa diodes made from materials #5 and #6. The final fluence is $1.4 \cdot 10^{14}$ cm <sup>-2</sup> .                       |
|           | The plot (b) in logarithmic scale evidences the beneficial annealing (irradiation  |
|           | June '97) 121  |

| Fig. 6.12 | $N_{e\!f\!f}$ versus annealing time (20 °C equivalent) for planar and mesa diodes made from                   |
|-----------|---|
|           | epitaxial materials (#17 to #19). The final fluence is $1.8 \cdot 10^{14}$ cm <sup>-2</sup> . The plot (b) in |
|           | logarithmic scale evidences the beneficial annealing (irradiation August '97) 122                             |
| Fig. 6.13 | Reverse leakage current versus fluence for planar diodes made from standard                                   |
|           | materials with different resistivities (#1 and #2) 123  |
| Fig. 6.14 | $I_{vol}$ versus fluence for planar diodes made from FZ materials #4, #5 and #6124                            |
| Fig. 6.15 | $I_{vol}$ versus fluence for planar diodes made from epitaxial materials #17, #18                             |
|           | <i>and #19</i>  |
| Fig. 6.16 | $I_{vol}$ versus fluence for mesa diodes from the same standard silicon wafer (#5) and                        |
|           | from a weakly oxygenated wafer (#6)124  |
| Fig. 6.17 | $V_{FD}$ versus time at 80 °C for non-inverted standard (#3) and jet oxygenated (#11)                         |
|           | diodes after irradiation 125  |
| Fig.6.18  | Comparison between $V_{FD}$ measured after a fluence of $1 \cdot 10^{14}$ cm <sup>-2</sup> for three pairs of |
|           | diodes either submitted successively to 7 irradiations and annealing steps (circled                           |
|           | points) or irradiated directly to the final fluence and annealed in one step only.                            |
|           | Each annealing step is 4 min. at 80 °C 126  |
| Fig. 6.19 | Comparison between $V_{FD}$ as a function of the fluence measured $\approx 30$ min. after                     |
|           | irradiation and at the end of the beneficial annealing for two similar detectors 126                          |
| Fig. 6.20 | $N_{e\!f\!f}$ versus fluence for planar diodes made from standard (#5) and O-diffused                         |
|           | (#8,#9 and #10) silicon. The diffusion time of oxygen at 1150 $^\circ\!C$ is indicated in                     |
|           | the pictures  |
| Fig. 6.21 | $N_{eff}$ versus fluence for planar diodes made from epitaxial materials (#15) 128                            |
| Fig. 6.22 | Comparison of $N_{eff}$ versus fluence for planar diodes made from O diffused FZ                              |
|           | (#9) and epitaxial materials (#15)128   |
| Fig 6.23  | Comparison of $N_{eff}$ versus fluence between standard (#5) and NTD diodes (#23                              |
|           | #24)  |
| Fig. 6.24 | $N_{e\!f\!f}$ versus fluence for planar diodes made from FZ low resistivity standard (#3) and                 |
|           | <i>jet oxygenated (#11) silicon.</i>  |
| Fig 6.25  | $N_{eff}$ versus fluence for planar diodes made standard low resistivity silicon #3 and tin                   |
|           | enriched low resistivity silicon #13 129  |

| Fig. 6.26 | $N_{e\!f\!f}$ as a function of the fluence for planar diodes made from standard (#5),                     |
|-----------|---|
|           | carbonated (#7) and jet-oxygenated (#12) silicon  |
| Fig. 6.27 | $N_{e\!f\!f}$ versus fluence for planar diodes made from MACOM 100 $\mu m$ epitaxial silicon              |
|           | #14 (a) $5x5 \text{ mm}^2$ square diode (b) 1.36 cm <sup>2</sup> round device                             |
| Fig. 6.28 | $N_{eff}$ as a function of the annealing time at 60 °C for planar diode made from                         |
|           | standard (#5) and O-diffused (#8, #9 and #10) silicon. Irradiation fluence:                               |
|           | $1.5 \cdot 10^{14}  cm^{-2}$ . 131  |
| Fig. 6.29 | $N_{\rm eff}$ as a function of the time after irradiation for planar and mesa diode made from             |
|           | standard material (#5) and planar diodes made from jet-oxygenated silicon (#11):                          |
|           | (a) full scale (b) limited scale to evidence the beneficial annealing                                     |
| Fig. 6.30 | $I_{vol}$ as a function of fluence for planar diodes made from standard (#5) and oxygen                   |
|           | <i>diffused (#9) wafers.</i> 132  |
| Fig. 6.31 | $I_{vol}$ as a function of fluence for planar diodes made from similar epitaxial wafers                   |
|           | (#15)   |
| Fig. 6.32 | $I_{vol}$ as a function of fluence for planar diodes made from low resistivity (a) tin                    |
|           | enriched (#13) and (b) standard (#3) FZ wafers. The reverse current has been                              |
|           | annealed to 10 days equivalent at room temperature  |
| Fig. 6.33 | $I_{vol}$ as a function of fluence for planar diodes made from standard (#5), jet-                        |
|           | oxygenated (#12) and carbonated (#7) materials  |
| Fig. 6.34 | $I_{vol}$ as a function of fluence for planar diodes made from similar epitaxial wafers                   |
|           | (#14)   |
| Fig. 6.35 | Charge collection efficiency versus proton fluence for planar diodes made from                            |
|           | Standard (#2, #5) and weakly oxygenated (#6) materials  |
| Fig. 6.36 | Comparison between (a) $\beta$ values, (b) $\Phi_{inv}/N_{eff}(0)$ and (c) $g_y$ for various sets of mesa |
|           | and planar diodes made from a similar material and irradiated with protons (labels                        |
|           | # refer to Table 6.1) 137   |
| Fig. 6.37 | Comparison between $eta$ values for neutron irradiated diodes made from various                           |
|           | materials. Measurements performed (a) after 30-60 minutes irradiation and (b)                             |
|           | after an annealing step of 4' at 80 °C. The labels # refer to Table 6.2 139                               |
| Fig. 6.38 | $\beta$ versus resistivity for neutron irradiated diodes made from various materials. 140                 |

| Fig. 7.1  | Simulated specific energy loss of low-range protons in silicon  |
|-----------|---|
| Fig. 7.2  | Charge collection versus $V^{1/2}$ , recorded by an ADC, for (a) front and (b) rear   |
|           | illumination of a non-irradiated silicon detector with protons of different   |
|           | energies  |
| Fig. 7.3  | CCE as a function of $V^{1/2}$ for diodes of different thicknesses irradiated by protons  |
|           | to $\approx 7.5 \ 10^{13} \ \text{cm}^{-2}$ . The $\alpha$ source was positioned on the rear side. Diode thicknesses:   |
|           | (a) 147µm, (b) 303µm, (c) 503µm   |
| Fig. 7.4  | Charge collection (CC) versus $V^{1/2}$ for variously irradiated diodes illuminated by  |
|           | protons of different energies from a Van de Graaf accelerator [6.1]. The CC is  |
|           | recorded by an ADC in the case of front injection (column (a)) and rear injection   |
|           | (column (b)) 145  |
| Fig. 7.5  | $V_{80}$ as a function of fluence for front and rear injection of low range protons:  |
|           | (a) 1 MeV (b) 2.5 MeV protons   |
| Fig. 7.6  | Shape of the LED pulse measured with a PM   |
| Fig 7.7   | CCE as a function of $V^{1/2}$ for front and rear illumination of non-irradiated (a)  |
|           | <i>n-type and (b) p-type diodes.</i>  |
| Fig. 7.8  | Signal pulse shape in a non-irradiated n-type diode. (a) Front illumination (b)   |
|           | Rear illumination from 80 to 95 volts (c) Rear illumination from 95 to 150 volts.   |
|           | $V_{FD} = 105 \ volts.$   |
| Fig. 7.9  | Peaking time versus $V^{1/2}$ for a non-irradiated and irradiated (low fluences) diodes   |
|           | for front LED illumination 150  |
| Fig. 7.10 | <i>Peaking time</i> $(t_p)$ <i>versus</i> $(V/V_{FD})^{1/2}$ <i>for rear injection in</i> ( <i>a</i> ) <i>n</i> -type and ( <i>b</i> ) <i>p</i> -type             |
|           | non irradiated diodes 151   |
| Fig. 7.11 | <i>CCE</i> versus $V^{1/2}$ for front and rear illumination of n-type irradiated (non-inverted)   |
|           | <i>diodes:</i> (a) $\Phi = 1.0 \cdot 10^{12} \text{ cm}^{-2}$ ( $\Phi < \Phi_{inv}$ ), (b) $\Phi = 1.5 \cdot 10^{13} \text{ cm}^{-2}$ ( $\Phi < \Phi_{inv}$ ) 151 |
| Fig.7.12  | CCE versus $V^{1/2}$ for an n-type diode irradiated up to $\Phi = 1.0 \cdot 10^{14} \text{ cm}^{-2}$ ( $\Phi > \Phi_{inv}$ ).                                     |
|           | (a) rear illumination (b) front illumination  |

- Fig. 7.15 Signal pulses for 1.10<sup>14</sup> cm<sup>-2</sup> irradiated diode illuminated by red LED light.
  (a) Front illumination: 10-40 V (b) Front illumination: 45-75 V
  (c) Front illumination: 80-180 V (d) Rear illumination 5-150 V. V<sub>FD</sub> = 70 volts... 153

- Fig. 7.21 Peaking time of the second peak (t<sub>pf</sub>) as a function of (V/V<sub>FD</sub>)<sup>1/2</sup> for front illumination of three heavily irradiated diodes: (a) 1.110<sup>14</sup> cm<sup>-2</sup> (b)1.710<sup>14</sup> cm<sup>-2</sup>
  (c) 2.910<sup>14</sup> cm<sup>-2</sup>.
  158

| Fig. 7.26 | Concentration of free majority carriers (holes) as a function of depth for heavily   |     |
|-----------|--|-----|
|           | irradiated detectors at different values of the applied bias                         | 162 |
| Fig. 7.27 | Simulated values [7.6] of the electric field at 100, 150 and 200 $\mu m$ depths as a |     |
|           | function of $V^{1/2}$  | 163 |

#### List of tables

#### **Chapter 1**

Table 1.1 Annual fluxes expected in silicon due to various damaging particles, expressed as the 1 MeV Equivalent neutron flux as a function of radial position for the ATLAS inner tracker. Flux units of the damaging particles are 10<sup>13</sup> (1 MeV) neutrons cm<sup>-2</sup> yr<sup>-1</sup>.

#### Chapter 2

| Table 2.1 | Difference between the bottom of the conduction band $(E_c)$ , the top of the valence     |
|-----------|---|
|           | band $(E_V)$ and the impurity level $(E_L)$ for the most important donors and acceptor is |
|           | silicon   |

| Table 3.1 | Hardness factor for the normalisation to the 1MeV neutron fluence for the two        |    |
|-----------|--|----|
|           | facilities used for the irradiation 5  | 9  |
| Table 3.2 | A few defect reactions in silicon. The subscript i stands for interstitial, s for    |    |
|           | substitutional, I for Si interstitial, V for vacancy, C for carbon, O for Oxygen and | D  |
|           | for phosphorus   | 51 |
| Table 3.3 | Identified defect states with their energy levels in eV                              | 1  |
| Table 3.4 | Fitting parameters for the annealing at room temperature of the reverse current      |    |

#### **Chapter 4**

Table 4.1 Different components of the reverse current.80

#### **Chapter 5**

| Table 5.1 | Diffusion parameters for boron and phosphorus in silicon found by different                 |   |
|-----------|---|---|
|           | workers [5.13]  | 3 |
| Table 5.2 | Diffusion parameters and solubility for O, C and Sn in silicon [5.13] 10                    | 6 |
| Table 5.3 | Tested silicon materials. Labels (*) indicate the analysis method used for the              |   |
|           | impurity concentrations: <sup>(a)</sup> Fourier Transform Infrared Spectroscopy (FTIR) at   |   |
|           | room temperature, <sup>(b)</sup> FTIR at 5K, <sup>(c)</sup> Secondary Ion Mass Spectrometry |   |
|           | (SIMS) profiling and <sup>(d)</sup> SIMS bulk measurement                                   | 3 |

#### **Chapter 6**

Table 6.1 Radiation hardness parameters extracted from the proton irradiation data...... 136
Table 6.2 Radiation hardness parameters extracted from the neutron irradiation data: measurements performed (a) 30-60' after irradiation and (b) after 4' at 80 °C... 138

#### **Chapter 7**

| Table 7.2 | Values of the velocity and of the electric field in the quasi-neutral bulk (QNB)      |
|-----------|---|
|           | bulk  |
| Table 7.3 | Values of the $v_M$ and $E_M$ for three heavily irradiated diodes                     |
| Table 7.4 | Comparison between $N_{eff}$ for three heavily irradiated diodes calculated using the |
|           | <i>C-V and the CCE methods.</i> 162   |